Figure 2. Block Diagram

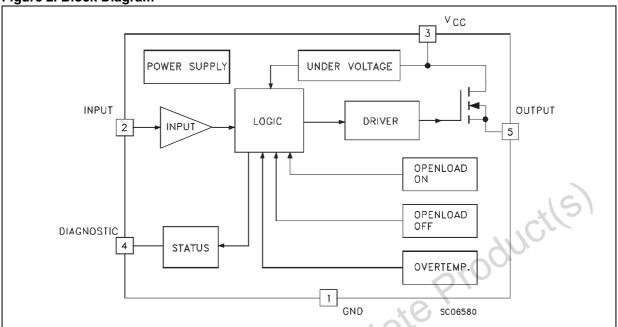


Table 3. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	40	V
lout	Output Current (cont.) at T _c = 85 °C	20	Α
I _{OUT} (RMS)	RMS Output Current at T _c = 85 °C	20	Α
I _R	Reverse Output Current at T _c = 85 °C (f > 1Hz)	-20	Α
I _{IN}	Input Current	±10	mA
- V _{CC}	Reverse Supply Voltage	-4	V
ISTAT	Status Current	±10	mA
V _{ESD}	Electrostatic Discharge (1.5 kΩ, 100 pF)	2000	V
P _{tot}	Power Dissipation at T _c = 25 °C	82	W
Q T _j	Junction Operating Temperature	-40 to 150	°C
T _{stg}	Storage Temperature	-55 to 150	°C

Figure 3. Connection Diagram

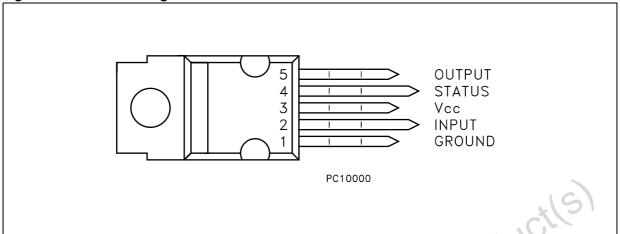


Figure 4. Current and Voltage Conventions

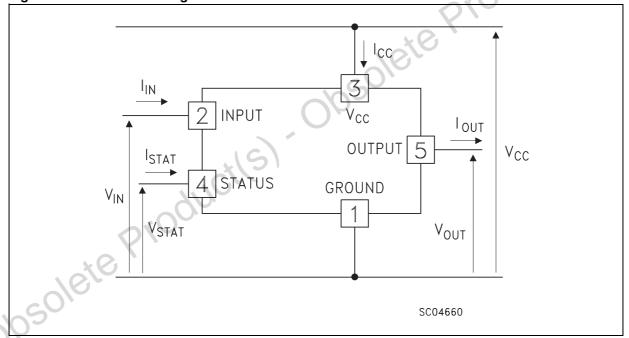


Table 4. Thermal Data

Symbol	Parameter		Value	Unit
R _{thj-case}	Thermal Resistance Junction-case	Max	1.5	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	60	°C/W

ELECTRICAL CHARACTERISTICS

(8 < V_{CC} < 16 V; -40 \leq T_{j} \leq 125 $^{\circ}C$ unless otherwise specified)

Table 5. Power

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{CC}	Supply Voltage		6	13	26	V
In ⁽³⁾	Nominal Current	$T_c = 85 ^{\circ}\text{C} V_{DS(on)} \le 0.5; V_{CC} = 13 V$	5.6		8.8	Α
Ron	On State Resistance	I _{OUT} = I _n ; V _{CC} = 13 V; T _j = 25 °C	0.038		0.06	Ω
Is	Supply Current	Off State; V_{CC} = 13 V; $T_j \ge$ 25 °C		25	50	μΑ
V _{DS(MAX)}	Maximum Voltage Drop	I _{OUT} = 20 A; V _{CC} = 13 V; T _c = 85 °C	1		1.8	V
Ri	Output to GND Internal Impedance	T _j = 25 °C	5	10	20	ΚΩ

Note: 3. Nominal current according to ISO definition for high side automotive switch The Nominal Current is the current at T_c = 85 °C for battery voltage of 13V which produces a voltage drop of 0.5 V.

Table 6. Switching

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
t _{d(on)} ⁽⁴⁾	Turn-on Delay Time Of Output Current	$R_{load} = 1.6 \Omega$	5	50	500	μs
t _r ⁽⁴⁾	Rise Time Of Output Current	$R_{load} = 1.6 \Omega$	40	100	680	μs
t _{d(off)} ⁽⁴⁾	Turn-off Delay Time Of Output Current	$R_{load} = 1.6 \Omega$	10	100	500	μs
t _f (4)	Fall Time Of Output Current	$R_{load} = 1.6 \Omega$	40	100	680	μs
(di/dt) _{on}	Turn-on Current Slope	$R_{load} = 1.6 \Omega; V_{CC} = 13 V$	0.008		0.1	A/µs
(di/dt) _{off}	Turn-off Current Slope	$R_{load} = 1.6 \Omega; V_{CC} = 13 V$	0.008		0.1	A/µs
V _{demag}	Inductive Load Clamp Voltage	$R_{load} = 1.6 \Omega$; L = 1 mH	-24	-18	-14	V

Note: 4. See Switchig Time Waveforms.

Table 7. Logic Input

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{IL}	Input Low Level Voltage				1.5	V
V _{IH}	Input High Level Voltage		3.5		Note 5	V
V _{I(hyst)}	Input Hysteresis Voltage		0.2	1	1.5	V
I _{IN}	Input Current	V _{IN} = 5 V; T _j = 25 °C			100	μΑ
V _{ICL}	Input Clamp Voltage	I _{IN} = 10 mA I _{IN} = -10 mA	5	6 -0.7	7	V V

Note: 5. The V_{IH} is internally clamped at 6V about. It is possible to connect this pin to an higher voltage via an external resistor calculated to not exceed 10 mA at the input pin.

ELECTRICAL CHARACTERISTICS (cont'd)

Table 8. Protections and Diagnostics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{STAT}	Status Voltage Output Low	I _{STAT} = 1.6 mA			0.4	V
V _{USD}	Under Voltage Shut Down		3.5	5	6	V
V _{SCL}	Status Clamp Voltage	I _{STAT} = 10 mA I _{STAT} = -10 mA	5	6 -0.7	7	V V
T _{TSD}	Thermal Shut-down Temperature		140	160	180	°C
T _{SD(hyst.)}	Thermal Shut-down Hysteresis			15	50	°C
T _R	Reset Temperature		125		.10	°C
V _{OL} ⁽⁶⁾	Open Voltage Level	Off-State	2.5	3.8	5	٧
l _{OL}	Open Load Current Level	On-State	0.15	71	0.85	Α
t _{povl} ⁽⁷⁾	Status Delay		210	5	10	μs
t _{pol} ⁽⁷⁾	Status Delay		50	400	2500	μs

Note: 6. $I_{OL(off)} = (V_{CC} - V_{OL})/R_{OL}$ (see figure 5). 7. $t_{poyl} t_{pol}$: ISO definition (see figure 6).

Figure 5. Note 6 relevant figure

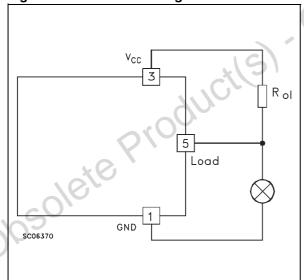
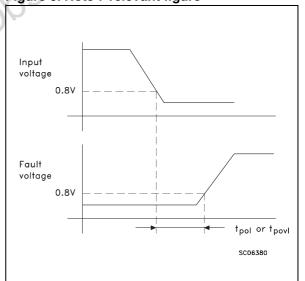
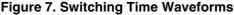
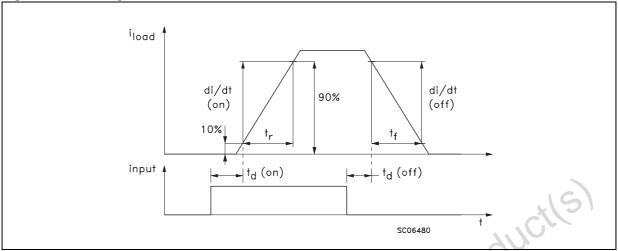


Figure 6. Note 7 relevant figure







FUNCTIONAL DESCRIPTION

The device has a diagnostic output which indicates open load in on-state, open load in offstate, over temperature conditions and stuck-on to $V_{\rm CC}$.

From the falling edge of the input signal, the status output, initially low to signal a fault condition (overtemperature or open load on-state), will go back to a high state with a different delay in case of overtemperature (t_{povl}) and in case of open load respectively. This feature allows to (t_{pol}) discriminate the nature of the detected fault. To protect the device against short circuit and over current condition, the thermal protection turns the integrated Power MOS off at a minimum junction temperature of 140 °C. When this temperature returns to 125 °C the switch is automatically turned on again. In short circuit the protection reacts with virtually no delay, the sensor being located inside the Power MOS area. An internal function of the devices ensures the fast demagnetization of inductive loads with a typical voltage (V_{demag}) of -18V. This function allows to greatly reduces the power dissipation according to the formula:

 $P_{dem} = 0.5 \cdot L_{load} \cdot (I_{load})^2 \cdot [(V_{CC} + V_{demag})/V_{demag}] \cdot f$

where f = switching frequency and

V_{demag} = demagnetization voltage

The maximum inductance which causes the chip temperature to reach the shut-down temperature in a specified thermal environment is a function of

the load current for a fixed V_{CC} , V_{demag} and f according to the above formula. In this device if the GND pin is disconnected, with V_{CC} not exceeding 16V, it will switch off.

PROTECTING THE DEVICE AGAINST REVERSE BATTERY

The simplest way to protect the device against a continuous reverse battery voltage (-26V) is to insert a Schottky diode between pin 1(GND) and ground, as shown in the typical application circuit (Figure 10).

The consequences of the voltage drop across this diode are as follows:

- If the input is pulled to power GND, a negative voltage of -V_f is seen by the device. (V_{IL}, V_{IH} thresholds and V_{STAT} are increased by V_f with respect to power GND).
- The undervoltage shutdown level is increased by V_f.

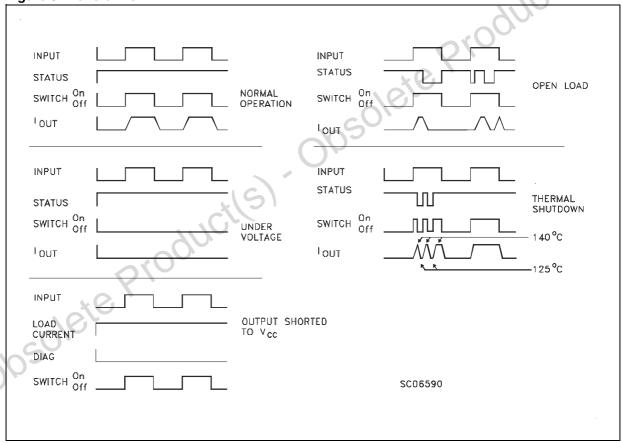
If there is no need for the control unit to handle external analog signals referred to the power GND, the best approach is to connect the reference potential of the control unit to node [1] (see application circuit in Figure 10), which becomes the common signal GND for the whole control board avoiding shift of V_{IH} , V_{IL} and V_{STAT} . This solution allows the use of a standard diode.

Table 9. Truth Table

	Input	Output	Diagnostic
Normal Operation	L H	L H	H H
Over-temperature	X	L	L
Under-voltage	Х	L	Н
Short load to V _{CC}	H L	H H	L L
Open Load	H L	H	L L(8)

Note: 8. With an additional external resistor.

Figure 8. Waveforms



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Figure 9. Over Current Test Circuit

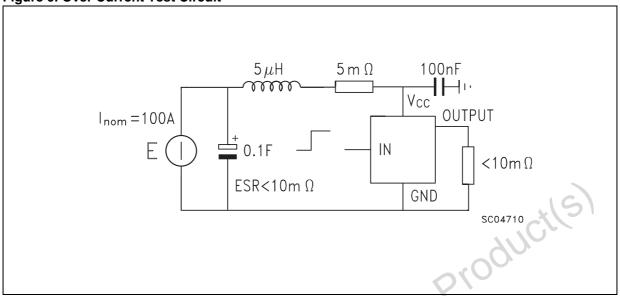
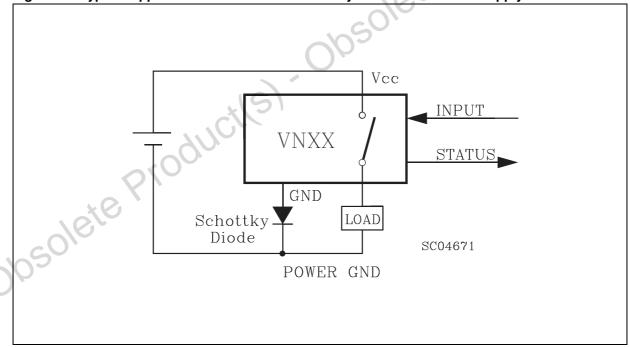


Figure 10. Typical Application Circuit With A Schottky Diode For Reverse Supply Protection



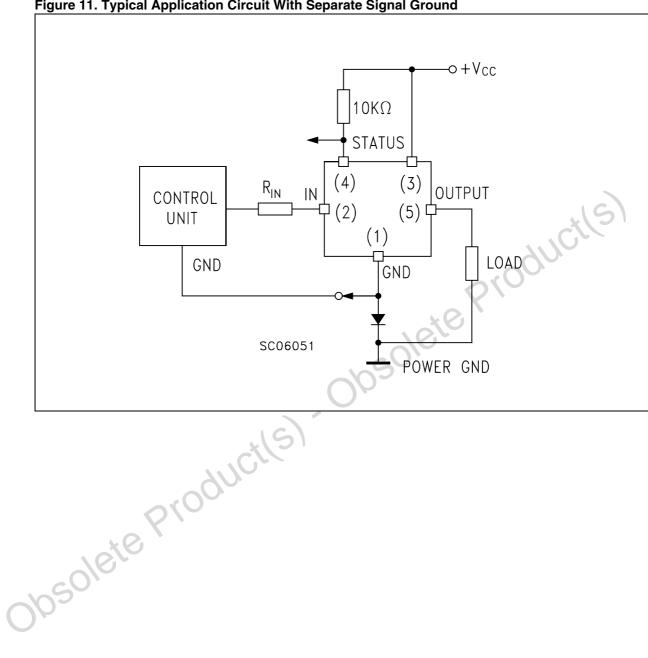


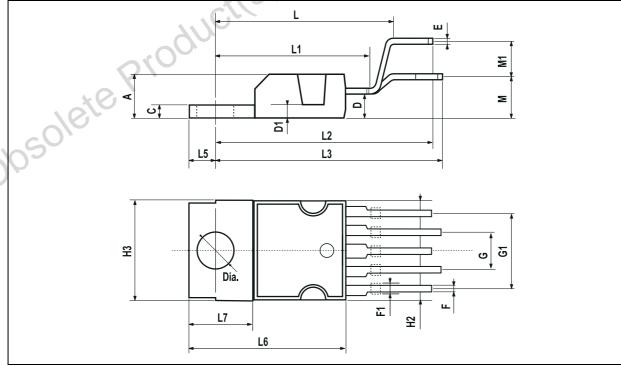
Figure 11. Typical Application Circuit With Separate Signal Ground

PACKAGE MECHANICAL

Table 10. PENTAWATT (vertical) Mechanical Data

Symbol		millimeters	
Symbol	Min	Тур	Max
Α			4.8
С			1.37
D	2.4		2.8
D1	1.2		1.35
E	0.35		0.55
F	0.8		1.05
F1	1		1,4
G	3.2	3.4	3.6
G1	6.6	6.8	7//4
H2			10.4
H3	10.05	0	10.4
L2	23.05	23.4	23.8
L3	25.3	25.65	26.1
L5	2.6		3
L6	15.1	1.60	15.8
L7	6	10	6.6
Dia.	3.65	7	3.85

Figure 12. PENTAWATT (vertical) Package Dimensions

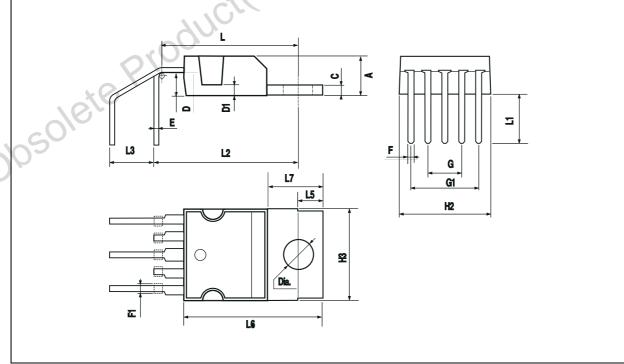


Note: Drawing is not to scale.

Table 11. PENTAWATT (horizontal) Mechanical Data

Symbol	,	millimeters	
Symbol	Min	Тур	Max
Α			4.8
С			1.37
D	2.4		2.8
D1	1.2		1.35
E	0.35		0.55
F	0.8		1.05
F1	1		1.4
G	3.2	3.4	3.6
G1	6.6	6.8	7.(5)
H2			10.4
H3	10.05		10.4
L	14.2		15
L1	5.7	0	6.2
L2	14.6		15.2
L3	3.5	101	4.1
L5	2.6		3
L6	15.1	105	15.8
L7	6	10	6.6
Dia.	3.65		3.85

Figure 13. PENTAWATT (horizontal) Package Dimensions

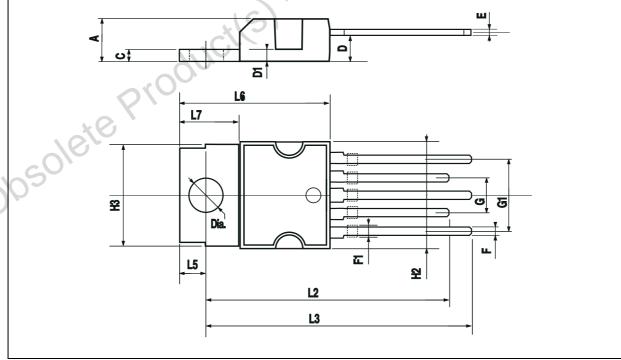


Note: Drawing is not to scale.

Table 12. PENTAWATT (in-line) Mechanical Data

Symbol		millimeters	
Symbol	Min	Тур	Max
A			4.8
С			1.37
D	2.4		2.8
D1	1.2		1.35
E	0.35		0.55
F	0.8		1.05
F1	1		1.4
G	3.2	3.4	3.6
G1	6.6	6.8	7.(5)
H2			10.4
H3	10.05		10.4
L2	23.05	23.4	23.8
L3	25.3	25.65	26.1
L5	2.6	1.0	3
L6	15.1	10/0	15.8
L7	6		6.6
Dia.	3.65	105	3.85

Figure 14. PENTAWATT (in-line) Package Dimensions



Note: Drawing is not to scale.

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REVISION HISTORY

Table 13. Revision History

Date	Revision	Description of Changes
September-1994	1	First Issue
18-June-2004	2	Stylesheet update. No content change.



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